

Title (en)  
READING CIRCUIT FOR RESISTIVE MEMORY

Title (de)  
LESESCHALTUNG FÜR RESISTIVEN SPEICHER

Title (fr)  
CIRCUIT DE LECTURE POUR MÉMOIRE RÉSISTIVE

Publication  
**EP 3227889 A1 20171011 (FR)**

Application  
**EP 15810692 A 20151201**

Priority  
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Abstract (en)  
[origin: WO2016087763A1] The invention relates to a circuit for reading a programmed resistive state of resistive elements (102) of a resistive memory (101), wherein each resistive element may be programmed to be in a first or a second resistive state (R<sub>max</sub>, R<sub>min</sub>), wherein the circuit comprises a current integrator (122) suitable for integrating a difference in current between a reading current (I<sub>R</sub>) flowing through a first of the resistive elements and a reference current (I<sub>REF</sub>).

IPC 8 full level  
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Citation (search report)  
See references of WO 2016087763A1

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**FR 1461717 A 20141201**; EP 15810692 A 20151201; FR 2015053273 W 20151201; US 201515531782 A 20151201